

Appl. No.: 09/504,660  
Reply to Office Action of October 17, 2003

Atty. Docket No.: RTN2-047PUS  
(formerly 07206-047001)

**REMARKS/ARGUMENTS**

Reconsideration is hereby requested.

Claim 32 points out that the transistor has a resistive layer disposed over the Schottky layer and a contact layer disposed over the resistive layer, *the contact layer having a first recess, and the resistive layer and the Schottky layer having a second recess.*

The claim stands rejected as being obvious over Hur et al. in view of Ando.

It is first noted that Hur et al. has a double recess, but both recesses are in the Schottky layer. Thus, Hur et al. does not have a device with *the contact layer having a first recess, and the resistive layer and the Schottky layer having a second recess.*

It is next noted that Ando is a single recess device and that the layer over the Schottky layer 96 in figure 9 is an *n doped* layer 97. The *n doped* layer 97 is not described as, nor is such *n doped* layer inherently, a resistive layer. Further, there is nothing in either Hur et al., or Ando, taken either singly or in combination, which suggests providing *both* the *resistive layer and the Schottky layer with a second recess.*

In the event any additional fee is required, please charge such amount to Patent and Trademark Office Deposit Account No. 50-0845.

1-15-04  
Date

Respectfully submitted,



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